

Silicon PNP Power Transistors

2SB1085

DESCRIPTION

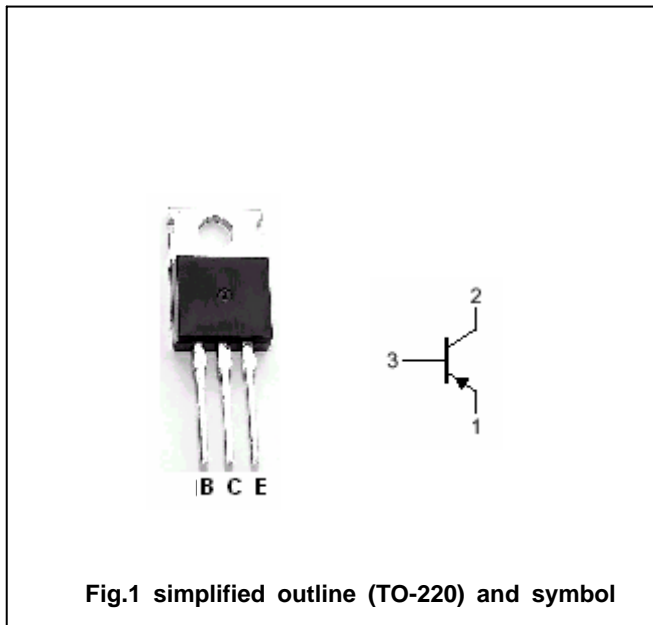
- With TO-220 package
- Complement to type 2SD1562
- Low collector saturation voltage

APPLICATIONS

- Designed for use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-120	V
$V_{CEO}$	Collector-emitter voltage	Open base	-120	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-1.5	A
$I_{CM}$	Collector current-peak		-3.0	A
$P_C$	Collector power dissipation	$T_C=25$	20	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-120			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-50 μA, I <sub>E</sub> =0	-120			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-50 μA, I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-1A; I <sub>B</sub> =-0.1A			-2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-1A; I <sub>B</sub> =-0.1A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-100V; I <sub>E</sub> =0			-1.0	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-4V; I <sub>C</sub> =0			-1.0	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-0.1A; V <sub>CE</sub> =-5V	60		320	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =-10V, f=1MHz		30		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.1A; V <sub>CE</sub> =-5V		50		MHz

◆ h<sub>FE</sub> classifications

D	E	F
60-120	100-200	160-320

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PACKAGE OUTLINE

